74AUP2G32

Low-power dual 2-input OR gate Rev. 7 — 23 January 2013

Product data sheet

General description 1.

The 74AUP2G32 provides dual 2-input OR function.

Schmitt trigger action at all inputs makes the circuit tolerant to slower input rise and fall times across the entire V_{CC} range from 0.8 V to 3.6 V.

This device ensures a very low static and dynamic power consumption across the entire V_{CC} range from 0.8 V to 3.6 V.

This device is fully specified for partial power-down applications using I_{OFF}. The I_{OFF} circuitry disables the output, preventing a damaging backflow current through the device when it is powered down.

Features and benefits 2.

- Wide supply voltage range from 0.8 V to 3.6 V
- High noise immunity
- Complies with JEDEC standards:
 - ◆ JESD8-12 (0.8 V to 1.3 V)
 - ◆ JESD8-11 (0.9 V to 1.65 V)
 - JESD8-7 (1.2 V to 1.95 V)
 - ◆ JESD8-5 (1.8 V to 2.7 V)
 - ◆ JESD8-B (2.7 V to 3.6 V)
- ESD protection:
 - HBM JESD22-A114F Class 3A exceeds 5 000 V
 - MM JESD22-A115-A exceeds 200 V
 - CDM JESD22-C101E exceeds 1000 V
- Low static power consumption; $I_{CC} = 0.9 \mu A$ (maximum)
- Latch-up performance exceeds 100 mA per JESD 78 Class II
- Inputs accept voltages up to 3.6 V
- Low noise overshoot and undershoot < 10 % of V_{CC}
- I_{OFF} circuitry provides partial Power-down mode operation
- Multiple package options
- Specified from -40 °C to +85 °C and -40 °C to +125 °C



3. Ordering information

Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74AUP2G32DC	–40 °C to +125 °C	VSSOP8	plastic very thin shrink small outline package; 8 leads; body width 2.3 mm	SOT765-1
74AUP2G32GT	–40 °C to +125 °C	XSON8	plastic extremely thin small outline package; no leads; 8 terminals; body 1 \times 1.95 \times 0.5 mm	SOT833-1
74AUP2G32GF	–40 °C to +125 °C	XSON8	extremely thin small outline package; no leads; 8 terminals; body 1.35 \times 1 \times 0.5 mm	SOT1089
74AUP2G32GD	–40 °C to +125 °C	XSON8	plastic extremely thin small outline package; no leads; 8 terminals; body 3 \times 2 \times 0.5 mm	SOT996-2
74AUP2G32GM	–40 °C to +125 °C	XQFN8	plastic, extremely thin quad flat package; no leads; 8 terminals; body 1.6 \times 1.6 \times 0.5 mm	SOT902-2
74AUP2G32GN	–40 °C to +125 °C	XSON8	extremely thin small outline package; no leads; 8 terminals; body 1.2 \times 1.0 \times 0.35 mm	SOT1116
74AUP2G32GS	–40 °C to +125 °C	XSON8	extremely thin small outline package; no leads; 8 terminals; body $1.35 \times 1.0 \times 0.35$ mm	SOT1203

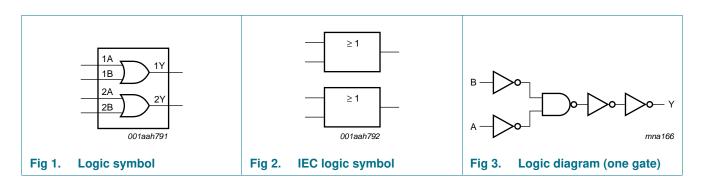
4. Marking

Table 2. Marking codes

Type number	Marking code ^[1]
74AUP2G32DC	p32
74AUP2G32GT	p32
74AUP2G32GF	pG
74AUP2G32GD	p32
74AUP2G32GM	p32
74AUP2G32GN	pG
74AUP2G32GS	pG

^[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

5. Functional diagram

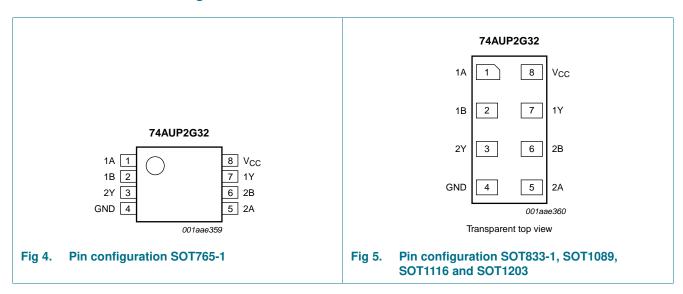


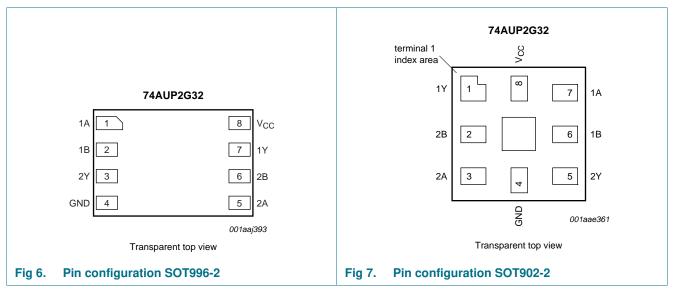
74AUP2G32

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6. Pinning information

6.1 Pinning





6.2 Pin description

Table 3. Pin description

Symbol	Pin	Pin				
	SOT765-1, SOT833-1, SOT1089, SOT996-2, SOT1116 and SOT1203	SOT902-2				
1A, 2A	1, 5	7, 3	data input			
1B, 2B	2, 6	6, 2	data input			
GND	4	4	ground (0 V)			
1Y, 2Y	7, 3	1, 5	data output			
V_{CC}	8	8	supply voltage			

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7. Functional description

Table 4. Function table[1]

Input		Output
nA	nB	nY
L	L	L
L	Н	Н
Н	L	Н
Н	Н	Н

^[1] H = HIGH voltage level; L = LOW voltage level.

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

					•
Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		-0.5	+4.6	V
I _{IK}	input clamping current	V _I < 0 V	-50	-	mA
VI	input voltage		<u>[1]</u> –0.5	+4.6	V
I _{OK}	output clamping current	V _O < 0 V	-50	-	mA
V _O	output voltage	Active mode and Power-down mode	<u>[1]</u> –0.5	+4.6	V
I _O	output current	$V_O = 0 V \text{ to } V_{CC}$	-	±20	mA
I _{CC}	supply current		-	+50	mA
I _{GND}	ground current		-50	-	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation	$T_{amb} = -40 ^{\circ}\text{C} \text{ to } +125 ^{\circ}\text{C}$	[2] -	250	mW

^[1] The minimum input and output voltage ratings may be exceeded if the input and output current ratings are observed.

9. Recommended operating conditions

Table 6. Operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		8.0	3.6	V
V _I	input voltage		0	3.6	V
V _O	output voltage	Active mode	0	V_{CC}	V
		Power-down mode; V _{CC} = 0 V	0	3.6	V
T _{amb}	ambient temperature		-40	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	$V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	0	200	ns/V

^[2] For VSSOP8 packages: above 110 °C the value of P_{tot} derates linearly with 8.0 mW/K. For XSON8 and XQFN8 packages: above 118 °C the value of P_{tot} derates linearly with 7.8 mW/K.

10. Static characteristics

Table 7. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
T _{amb} = 2	5 °C					
V_{IH}	HIGH-level input voltage	$V_{CC} = 0.8 \text{ V}$	$0.70 \times V_{CC}$	-	-	V
		V _{CC} = 0.9 V to 1.95 V	$0.65 \times V_{CC}$	-	-	V
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	1.6	-	-	V
		V _{CC} = 3.0 V to 3.6 V	2.0	-	-	V
V _{IL}	LOW-level input voltage	$V_{CC} = 0.8 \text{ V}$	-	-	$0.30 \times V_{CC}$	V
		V _{CC} = 0.9 V to 1.95 V	-	-	$0.35 \times V_{CC}$	V
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	-	-	0.7	V
		V _{CC} = 3.0 V to 3.6 V	-	-	0.9	V
V _{OH}	HIGH-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		$I_O = -20~\mu A;~V_{CC} = 0.8~V~to~3.6~V$	$V_{CC}-0.1$	-	-	V
		$I_{O} = -1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	$0.75 \times V_{CC}$	-	-	V
		$I_{O} = -1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	1.11	-	-	V
		$I_{O} = -1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	1.32	-	-	V
		$I_{O} = -2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	2.05	-	-	V
		$I_{O} = -3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.9	-	-	V
		$I_{O} = -2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.72	-	-	V
		$I_{O} = -4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.6	-	-	V
V_{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		I_O = 20 μ A; V_{CC} = 0.8 V to 3.6 V	-	-	0.1	V
		$I_O = 1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	-	-	$0.3 \times V_{CC}$	V
		$I_O = 1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	-	-	0.31	V
		$I_O = 1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	-	-	0.31	V
		$I_{O} = 2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.31	V
		$I_{O} = 3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.44	V
		$I_O = 2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.31	V
		$I_{O} = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.44	V
l _l	input leakage current	$V_I = GND$ to 3.6 V; $V_{CC} = 0$ V to 3.6 V	-	-	±0.1	μΑ
I _{OFF}	power-off leakage current	V_I or $V_O = 0$ V to 3.6 V; $V_{CC} = 0$ V	-	-	±0.2	μΑ
ΔI_{OFF}	additional power-off leakage current	V_{I} or $V_{O} = 0$ V to 3.6 V; $V_{CC} = 0$ V to 0.2 V	-	-	±0.2	μΑ
I _{CC}	supply current	$V_I = GND \text{ or } V_{CC}; I_O = 0 \text{ A};$ $V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	-	-	0.5	μΑ
Δl _{CC}	additional supply current	$V_I = V_{CC} - 0.6 \text{ V}; I_O = 0 \text{ A}; V_{CC} = 3.3 \text{ V}$	[1] -	-	40	μΑ
Cı	input capacitance	$V_{CC} = 0 \text{ V to } 3.6 \text{ V}; V_I = \text{GND or } V_{CC}$	-	0.6	-	pF
C _O	output capacitance	$V_O = GND; V_{CC} = 0 V$	-	1.3	-	pF

 Table 7.
 Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
T _{amb} = -	40 °C to +85 °C					
V _{IH}	HIGH-level input voltage	V _{CC} = 0.8 V	$0.70 \times V_{CC}$	-	-	٧
		V _{CC} = 0.9 V to 1.95 V	$0.65 \times V_{CC}$	-	-	٧
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	1.6	-	-	٧
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	2.0	-	-	٧
V _{IL}	LOW-level input voltage	$V_{CC} = 0.8 \text{ V}$	-	-	$0.30 \times V_{CC}$	٧
		$V_{CC} = 0.9 \text{ V to } 1.95 \text{ V}$	-	-	$0.35 \times V_{CC}$	٧
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	-	-	0.7	٧
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	-	-	0.9	٧
V _{OH}	HIGH-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		$I_{O} = -20 \mu A$; $V_{CC} = 0.8 \text{ V}$ to 3.6 V	$V_{CC}-0.1$	-	-	٧
		$I_O = -1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	$0.7 \times V_{CC}$	-	-	٧
		$I_O = -1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	1.03	-	-	٧
		$I_O = -1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	1.30	-	-	٧
		$I_{O} = -2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.97	-	-	٧
		$I_O = -3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.85	-	-	٧
		$I_O = -2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.67	-	-	٧
		$I_O = -4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.55	-	-	٧
V _{OL}	LOW-level output voltage	$V_{I} = V_{IH}$ or V_{IL}				
		$I_O = 20 \mu A$; $V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	-	-	0.1	٧
		I _O = 1.1 mA; V _{CC} = 1.1 V	-	-	$0.3 \times V_{CC}$	٧
		I _O = 1.7 mA; V _{CC} = 1.4 V	-	-	0.37	٧
		I _O = 1.9 mA; V _{CC} = 1.65 V	-	-	0.35	٧
		I _O = 2.3 mA; V _{CC} = 2.3 V	-	-	0.33	٧
		I _O = 3.1 mA; V _{CC} = 2.3 V	-	-	0.45	٧
		I _O = 2.7 mA; V _{CC} = 3.0 V	-	-	0.33	٧
		I _O = 4.0 mA; V _{CC} = 3.0 V	-	-	0.45	٧
l _l	input leakage current	$V_1 = GND \text{ to } 3.6 \text{ V}; V_{CC} = 0 \text{ V to } 3.6 \text{ V}$	-	-	±0.5	μΑ
l _{OFF}	power-off leakage current	V_{I} or $V_{O} = 0$ V to 3.6 V; $V_{CC} = 0$ V	-	-	±0.5	μA
ΔI_{OFF}	additional power-off leakage current	$V_1 \text{ or } V_O = 0 \text{ V to } 3.6 \text{ V};$ $V_{CC} = 0 \text{ V to } 0.2 \text{ V}$	-	-	±0.6	μΑ
lcc	supply current	V _I = GND or V _{CC} ; I _O = 0 A; V _{CC} = 0.8 V to 3.6 V	-	-	0.9	μΑ
Δl _{CC}	additional supply current	$V_I = V_{CC} - 0.6 \text{ V}; I_O = 0 \text{ A};$ $V_{CC} = 3.3 \text{ V}$	[1] -	-	50	μΑ
T _{amb} = -	40 °C to +125 °C					
V _{IH}	HIGH-level input voltage	$V_{CC} = 0.8 \text{ V}$	0.75 × V _{CC}	-	-	٧
	. •	V _{CC} = 0.9 V to 1.95 V	0.70 × V _{CC}		-	٧
		V _{CC} = 2.3 V to 2.7 V	1.6	-	-	٧
		V _{CC} = 3.0 V to 3.6 V	2.0			٧

 Table 7.
 Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{IL}	LOW-level input voltage	$V_{CC} = 0.8 \text{ V}$	-	-	$0.25 \times V_{CC}$	V
		V _{CC} = 0.9 V to 1.95 V	-	-	$0.30 \times V_{CC}$	V
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	-	-	0.7	V
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	-	-	0.9	V
V_{OH}	HIGH-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		$I_O = -20~\mu A;~V_{CC} = 0.8~V$ to 3.6 V	$V_{CC}-0.11$	-	-	V
		$I_{O} = -1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	$0.6 \times V_{CC}$	-	-	V
		$I_{O} = -1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	0.93	-	-	V
		$I_{O} = -1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	1.17	-	-	V
		$I_{O} = -2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.77	-	-	V
		$I_{O} = -3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.67	-	-	V
		$I_{O} = -2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.40	-	-	V
		$I_{O} = -4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.30	-	-	V
V _{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		$I_{O} = 20 \mu A$; $V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	-	-	0.11	V
		$I_{O} = 1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	-	-	$0.33 \times V_{CC}$	V
		$I_{O} = 1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	-	-	0.41	V
		$I_{O} = 1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	-	-	0.39	V
		$I_{O} = 2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.36	V
		$I_{O} = 3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.50	V
		$I_{O} = 2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.36	V
		$I_{O} = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.50	V
l _l	input leakage current	$V_I = GND$ to 3.6 V; $V_{CC} = 0$ V to 3.6 V	-	-	±0.75	μΑ
I _{OFF}	power-off leakage current	V_I or $V_O = 0$ V to 3.6 V; $V_{CC} = 0$ V	-	-	±0.75	μΑ
Δl _{OFF}	additional power-off leakage current	V_1 or $V_0 = 0$ V to 3.6 V; $V_{CC} = 0$ V to 0.2 V	-	-	±0.75	μΑ
lcc	supply current	V_I = GND or V_{CC} ; I_O = 0 A; V_{CC} = 0.8 V to 3.6 V	-	-	1.4	μΑ
Δl _{CC}	additional supply current	$V_{I} = V_{CC} - 0.6 \text{ V}; I_{O} = 0 \text{ A};$ $V_{CC} = 3.3 \text{ V}$	[1] -	-	75	μΑ

^[1] One input at V_{CC} – 0.6 V, other input at V_{CC} or GND.

11. Dynamic characteristics

Table 8. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 9.

Symbol	Parameter	Conditions			25 °C		-40) °C to +1	125 °C	Unit
				Min	Typ[1]	Max	Min	Max (85 °C)	Max (125 °C)	
$C_L = 5 p$	F									
t_{pd}	propagation delay	nA or nB to nY; see Figure 8	[2]							
		$V_{CC} = 0.8 \text{ V}$		-	16.8	-	-	-	-	ns
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$		2.4	5.1	10.9	2.1	11.9	13.2	ns
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$		1.6	3.6	6.6	1.4	7.5	8.3	ns
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$		1.4	3.0	5.2	1.2	6.0	6.6	ns
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		1.1	2.4	3.9	1.0	4.6	5.1	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$		1.0	2.1	3.5	0.9	4.1	4.6	ns
C _L = 10	pF									
t_{pd}	propagation delay	nA or nB to nY; see Figure 8	[2]							
		$V_{CC} = 0.8 \text{ V}$		-	20.3	-	-	-	-	ns
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$		2.3	5.9	12.7	2.1	13.8	15.2	ns
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$		1.9	4.2	7.7	1.7	8.7	9.6	ns
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$		1.7	3.5	6.0	1.5	6.9	7.7	ns
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		1.4	2.9	4.6	1.3	5.5	6.1	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$		1.3	2.7	4.3	1.2	5.0	5.5	ns
C _L = 15	pF									
t _{pd}	propagation delay	nA or nB to nY; see Figure 8	[2]							
		$V_{CC} = 0.8 V$		-	23.8	-	-	-	-	ns
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$		3.3	6.7	14.3	3.0	15.6	17.2	ns
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$		2.3	4.8	8.6	2.0	9.8	10.8	ns
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$		2.0	4.0	6.7	1.8	7.9	8.7	ns
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		1.7	3.3	5.3	1.6	6.3	6.9	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$		1.5	3.1	4.9	1.5	5.8	6.4	ns
C _L = 30	pF									
t _{pd}	propagation delay	nA or nB to nY; see Figure 8	[2]							
		$V_{CC} = 0.8 \text{ V}$		-	34.1	-	-	-	-	ns
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$		4.5	9.0	19.1	4.0	21.5	23.7	ns
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$		3.4	6.3	11.3	2.9	13.3	14.7	ns
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$		2.6	5.3	8.9	2.4	10.7	11.8	ns
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		2.3	4.4	7.0	2.2	8.4	9.3	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$		2.2	4.2	6.4	2.1	7.7	8.5	ns

Low-power dual 2-input OR gate

 Table 8.
 Dynamic characteristics ...continued

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 9.

Symbol	Parameter	Conditions			25 °C		-40) °C to +1	125 °C	Unit
				Min	Typ[1]	Max	Min	Max (85 °C)	Max (125 °C)	-
$C_L = 5 pl$	F, 10 pF, 15 pF and	30 pF						•		
C _{PD}	power dissipation	$f_i = 1 \text{ MHz}; V_I = \text{GND to } V_{CC}$	[3]							
	capacitance	$V_{CC} = 0.8 \text{ V}$		-	2.6	-	-	-	-	pF
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$		-	2.7	-	-	-	-	pF
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$		-	2.7	-	-	-	-	pF
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$		-	2.9	-	-	-	-	pF
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		-	3.3	-	-	-	-	pF
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$		-	3.7	-	-	-	-	pF

- [1] All typical values are measured at nominal V_{CC} .
- [2] t_{pd} is the same as t_{PLH} and t_{PHL} .
- [3] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

 $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma (C_L \times V_{CC}^2 \times f_o) \text{ where:}$

f_i = input frequency in MHz;

 $f_o = output frequency in MHz;$

C_L = output load capacitance in pF;

V_{CC} = supply voltage in V;

N = number of inputs switching;

 $\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of the outputs.

12. Waveforms

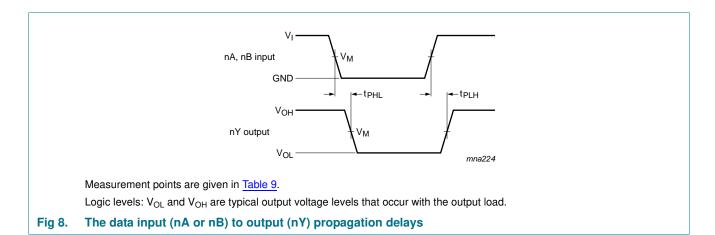
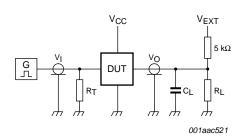


Table 9. Measurement points

Supply voltage	Output	Input		
V _{CC}	V _M	V _M	V _I	$t_r = t_f$
0.8 V to 3.6 V	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$	V _{CC}	≤ 3.0 ns

Low-power dual 2-input OR gate



Test data is given in Table 10.

Definitions for test circuit:

R_L = Load resistance.

 C_L = Load capacitance including jig and probe capacitance.

 R_T = Termination resistance should be equal to the output impedance Z_0 of the pulse generator.

 V_{EXT} = External voltage for measuring switching times.

Fig 9. Test circuit for measuring switching times

Table 10. Test data

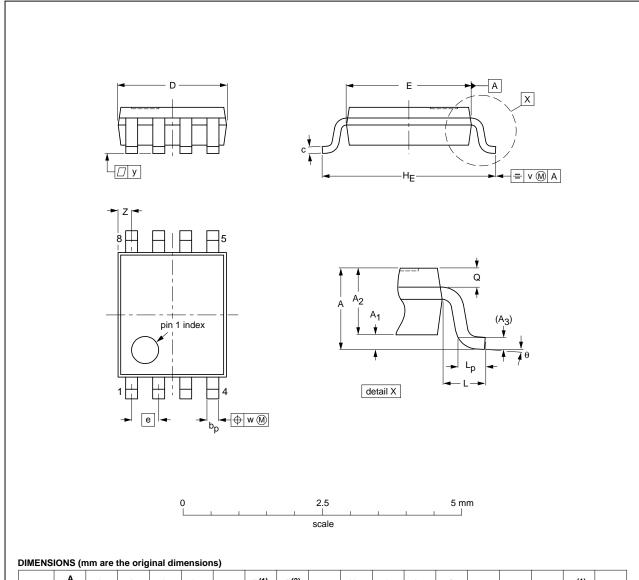
Supply voltage	Load		V _{EXT}				
V _{CC}	C _L	R _L [1]	t _{PLH} , t _{PHL}	t _{PZH} , t _{PHZ}	t _{PZL} , t _{PLZ}		
0.8 V to 3.6 V	5 pF, 10 pF, 15 pF and 30 pF	5 k Ω or 1 M Ω	open	GND	$2 \times V_{CC}$		

[1] For measuring enable and disable times R_L = 5 k Ω , for measuring propagation delays, set-up and hold times and pulse width R_L = 1 M Ω .

13. Package outline

VSSOP8: plastic very thin shrink small outline package; 8 leads; body width 2.3 mm

SOT765-1



UNIT	A max.	A ₁	A ₂	А3	bp	С	D ⁽¹⁾	E ⁽²⁾	е	HE	L	Lp	Q	v	w	у	Z ⁽¹⁾	θ
mm	1	0.15 0.00	0.85 0.60	0.12	0.27 0.17	0.23 0.08	2.1 1.9	2.4 2.2	0.5	3.2 3.0	0.4	0.40 0.15	0.21 0.19	0.2	0.13	0.1	0.4 0.1	8° 0°

Notes

- Plastic or metal protrusions of 0.15 mm maximum per side are not included.
- 2. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

OUTLINE		REFER	EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT765-1		MO-187				02-06-07

Fig 10. Package outline SOT765-1 (VSSOP8)

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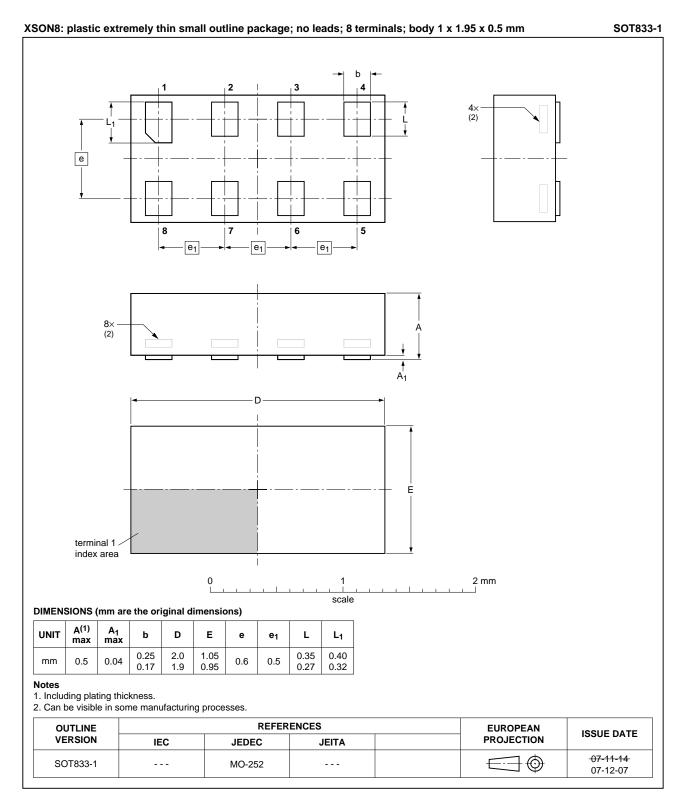


Fig 11. Package outline SOT833-1 (XSON8)

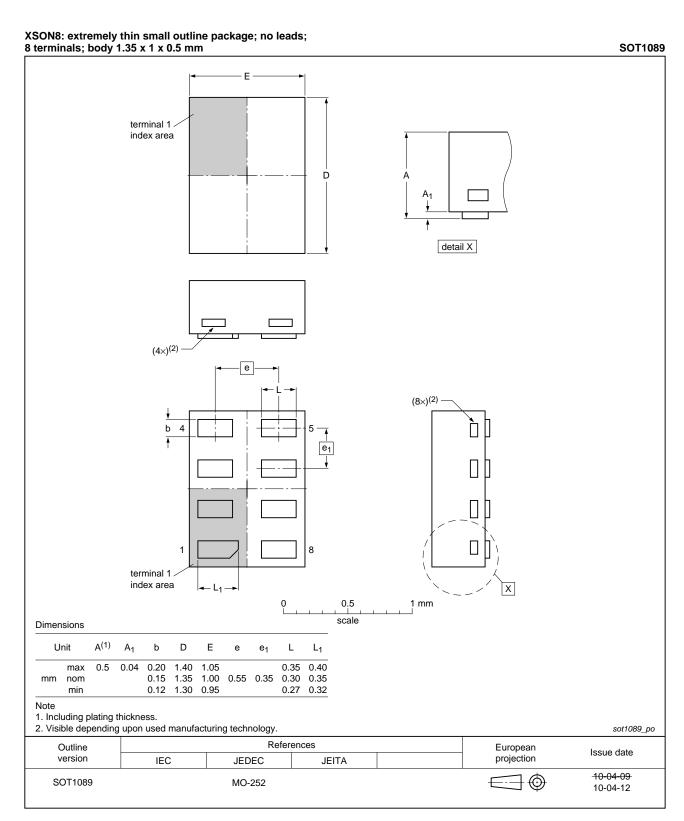


Fig 12. Package outline SOT1089 (XSON8)

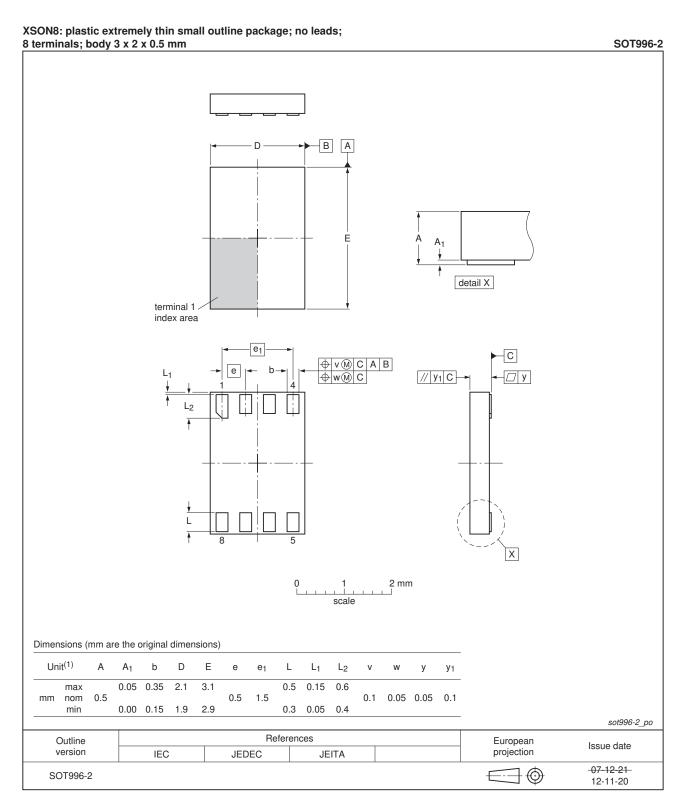


Fig 13. Package outline SOT996-2 (XSON8)

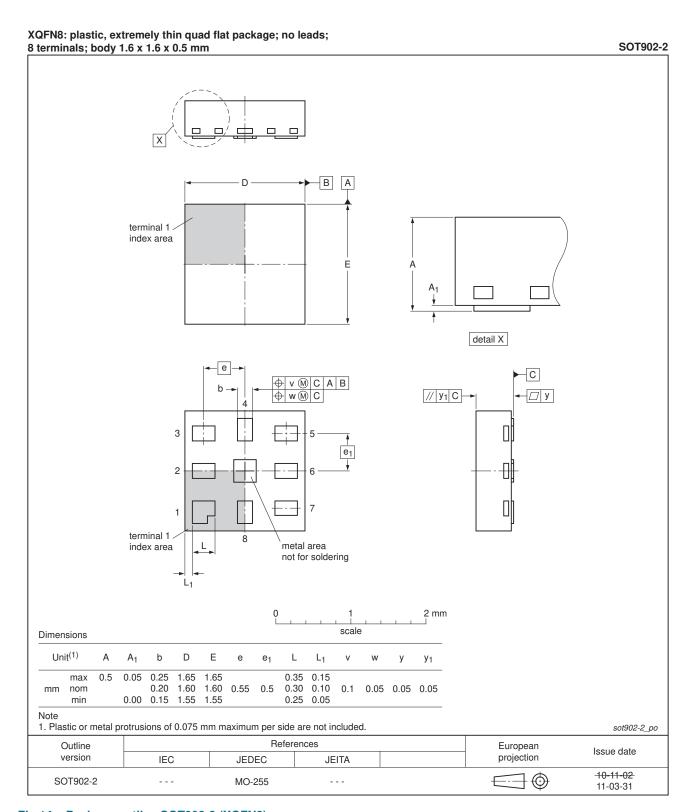


Fig 14. Package outline SOT902-2 (XQFN8)

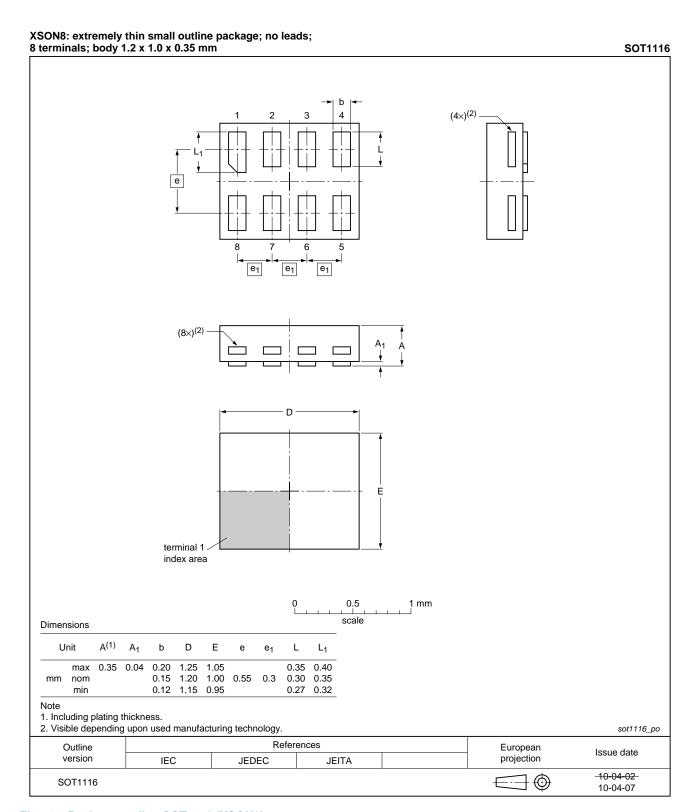


Fig 15. Package outline SOT1116 (XSON8)

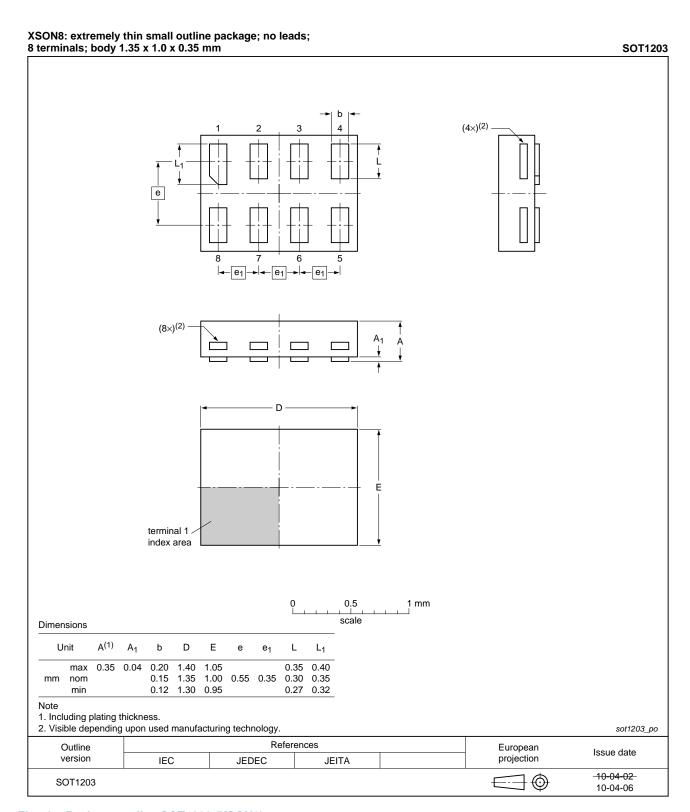


Fig 16. Package outline SOT1203 (XSON8)

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14. Abbreviations

Table 11. Abbreviations

Acronym	Description
CDM	Charged Device Model
DUT	Device Under Test
ESD	ElectroStatic Discharge
НВМ	Human Body Model
MM	Machine Model

15. Revision history

Table 12. Revision history

	-			
Document ID	Release date	Data sheet status	Change notice	Supersedes
74AUP2G32 v.7	20130123	Product data sheet	-	74AUP2G32 v.6
Modifications:	 For type nu 	mber 74AUP2G32GD XSON8	U has changed to XS	SON8.
74AUP2G32 v.6	20120605	Product data sheet	-	74AUP2G32 v.5
74AUP2G32 v.5	20111206	Product data sheet	-	74AUP2G32 v.4
74AUP2G32 v.4	20101021	Product data sheet	-	74AUP2G32 v.3
74AUP2G32 v.3	20090108	Product data sheet	-	74AUP2G32 v.2
74AUP2G32 v.2	20080228	Product data sheet	-	74AUP2G32 v.1
74AUP2G32 v.1	20061006	Product data sheet	-	-

16. Legal information

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Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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Low-power dual 2-input OR gate

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